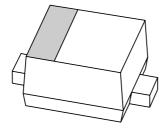
DISCRETE SEMICONDUCTORS

DATA SHEET



BAP65-01 Silicon PIN diode

Preliminary specification

2001 Nov 01





Silicon PIN diode BAP65-01

FEATURES

- High voltage, current controlled
- RF resistor for RF switches
- Low diode capacitance
- Low diode forward resistance (low loss)
- Very low series inductance.

APPLICATIONS

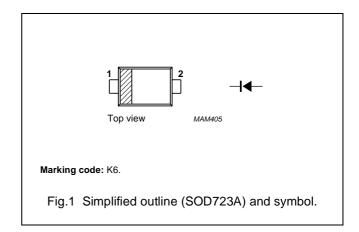
- · RF attenuators and switches
- · Bandswitch for TV tuners
- Series diode for mobile communication transmit/receive switch.

DESCRIPTION

Planar PIN diode in a SOD723A ultra small SMD plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage		_	30	V
I _F	continuous forward current		_	100	mA
P _{tot}	total power dissipation	T _s ≤ 90 °C	_	315	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-65	+150	°C

Philips Semiconductors Preliminary specification

Silicon PIN diode BAP65-01

ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	forward voltage	I _F = 50 mA	0.9	1.1	V
I _R	reverse leakage current	V _R = 20 V	_	20	nA
C _d	diode capacitance	V _R = 0 V; f = 1 MHz	0.61	_	pF
		V _R = 1 V; f = 1 MHz	0.48	0.9	pF
		V _R = 3 V; f = 1 MHz	0.43	0.8	pF
		V _R = 20 V; f = 1 MHz	0.375	_	pF
r _D	diode forward resistance	$I_F = 1 \text{ mA}; f = 100 \text{ MHz}$	1.0	_	Ω
		$I_F = 5 \text{ mA}$; $f = 100 \text{ MHz}$; note 1	0.6	0.95	Ω
		I _F = 10 mA; f = 100 MHz; note 1	0.5	0.9	Ω
		$I_F = 100 \text{ mA}$; $f = 100 \text{ MHz}$	0.3	_	Ω
S ₂₁ ²	isolation	V _R = 0; f = 900 MHz	9.4	_	dB
		$V_R = 0$; $f = 1800 \text{ MHz}$	5.5	_	dB
		$V_R = 0$; $f = 2450 \text{ MHz}$	4.1	_	dB
S ₂₁ ²	insertion loss	$I_F = 1 \text{ mA}; f = 900 \text{ MHz}$	0.10	_	dB
		$I_F = 1 \text{ mA}; f = 1800 \text{ MHz}$	0.12	_	dB
		$I_F = 1 \text{ mA}$; $f = 2450 \text{ MHz}$	0.15	_	dB
$ s_{21} ^2$	insertion loss	$I_F = 5 \text{ mA}; f = 900 \text{ MHz}$	0.08	_	dB
		$I_F = 5 \text{ mA}$; $f = 1800 \text{ MHz}$	0.10	_	dB
		$I_F = 5 \text{ mA}$; $f = 2450 \text{ MHz}$	0.12	_	dB
S ₂₁ ²	insertion loss	$I_F = 10 \text{ mA}; f = 900 \text{ MHz}$	0.06	_	dB
		I _F = 10 mA; f = 1800 MHz	0.09	_	dB
		I _F = 10 mA; f = 2450 MHz	0.11	_	dB
S ₂₁ ²	insertion loss	I _F = 100 mA; f = 900 MHz	0.05	_	dB
		I _F = 100 mA; f = 1800 MHz	0.08	_	dB
		I _F = 100 mA; f = 2450 MHz	0.10	_	dB
τ∟	charge carrier life time	when switched from I_F = 10 mA to I_R = 6 mA; R_L = 100 Ω ; measured at I_R = 3 mA	0.17	_	μs
L _S	series inductance	I _F = 100 mA; f = 100 MHz	0.6	_	nH
	•	•			

Note

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to soldering point	190	K/W

Silicon PIN diode BAP65-01

GRAPHICAL DATA

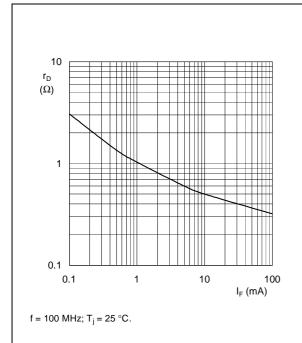
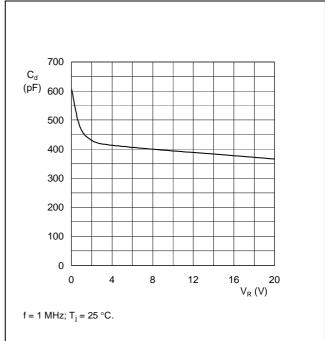
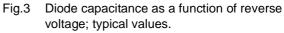
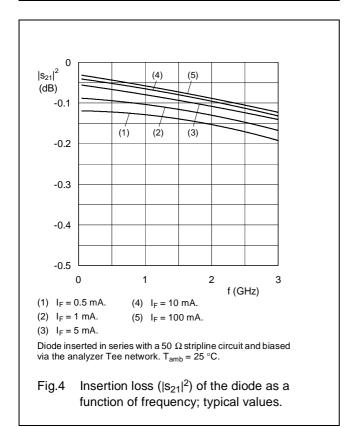
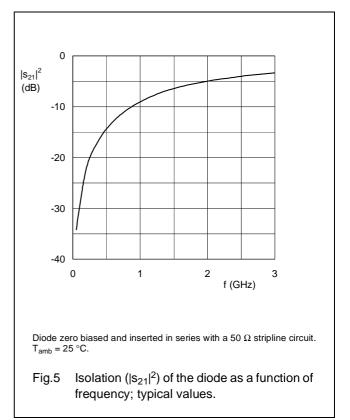


Fig.2 Forward resistance as a function of forward current; typical values.



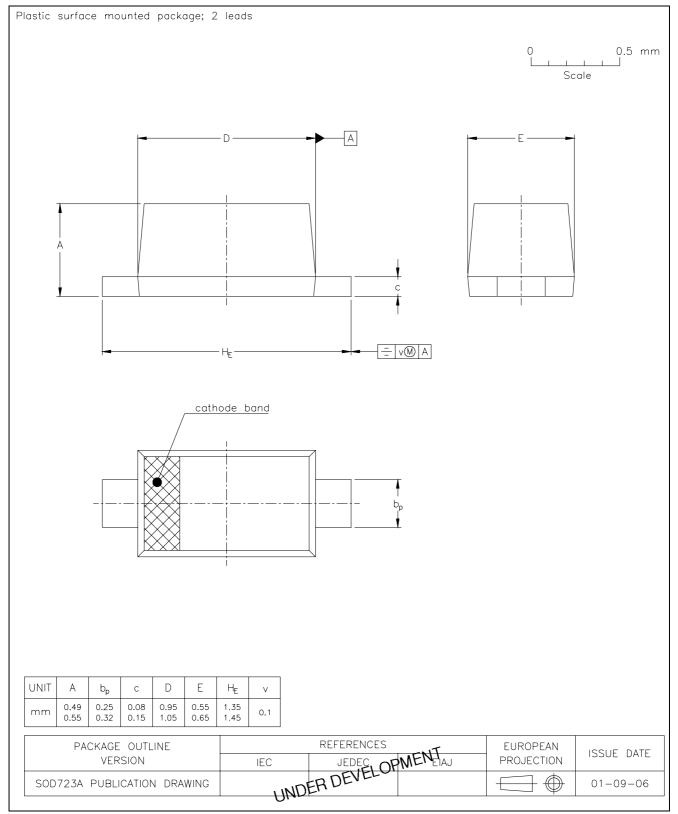






Silicon PIN diode BAP65-01

PACKAGE OUTLINE SOD723A



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Silicon PIN diode BAP65-01

DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

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